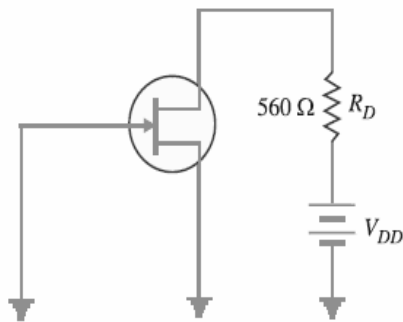


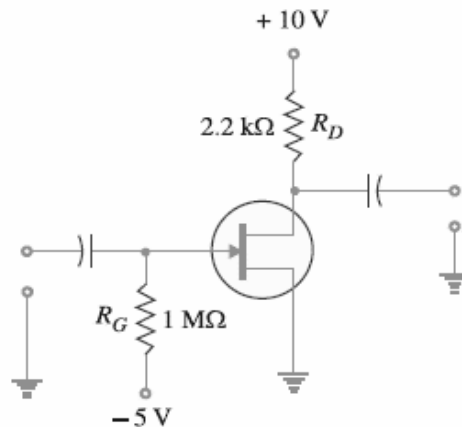
Electronic Devices

Sheet #7

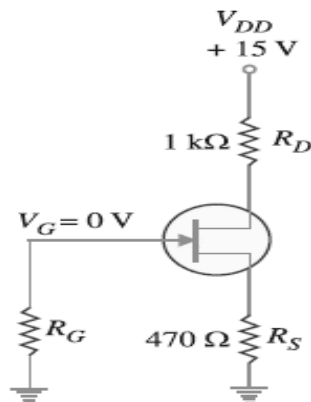
1. For the JFET shown, $V_{GS}(\text{off}) = -4\text{ V}$ and $I_{DSS} = 12\text{ mA}$. Determine the minimum value of V_{DD} required to put the device in the constant-current region of operation.



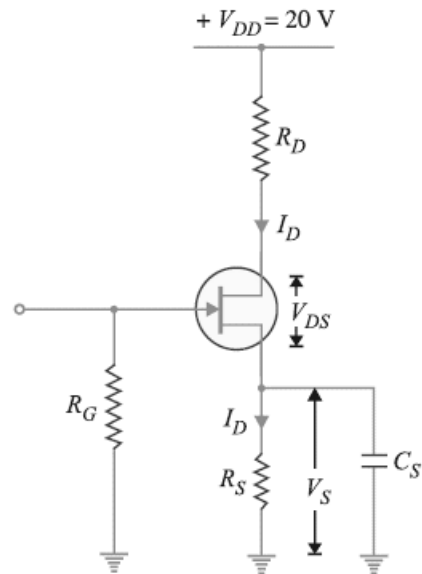
2. A JFET has values of $V_{GS}(\text{off}) = -8\text{ V}$ and $I_{DSS} = 16\text{ mA}$. Determine the values of V_{GS} , I_D and V_{DS} for the circuit.



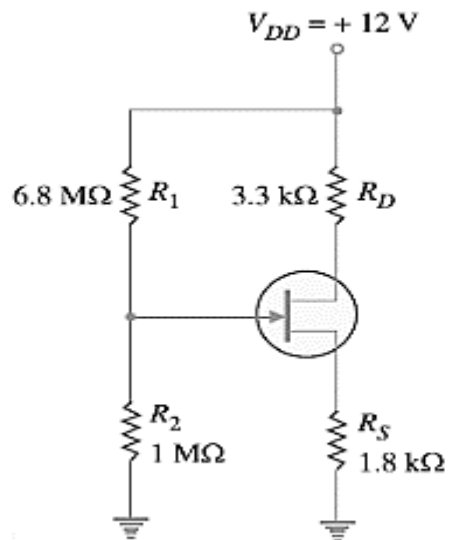
3. Find V_{DS} and V_{GS} in circuit shown, given that $I_D = 5\text{ mA}$.



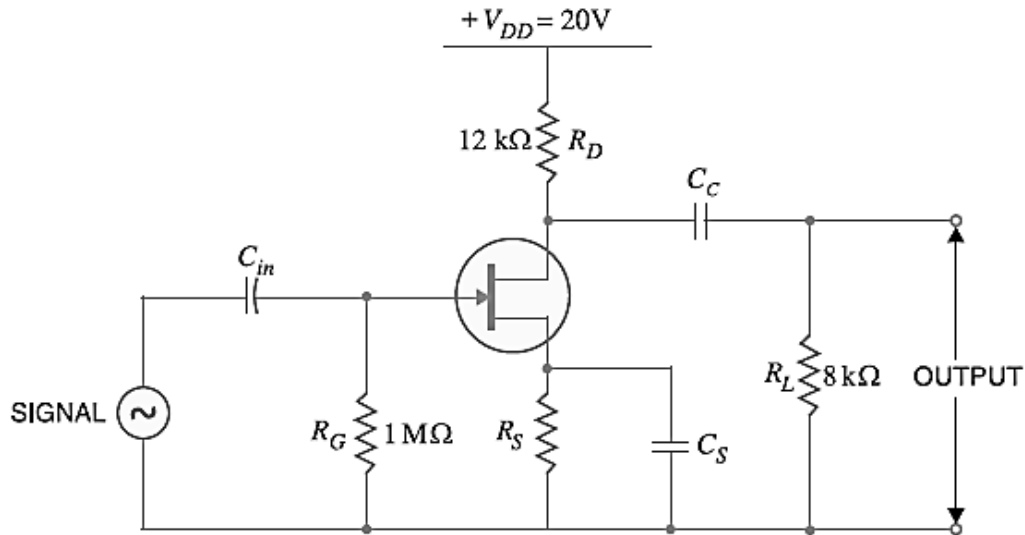
4. In a self-bias n-channel JFET, the operating point is to be set at $I_D = 1.5$ mA and $V_{DS} = 10$ V. The JFET parameters are $I_{DSS} = 5$ mA and $V_{GS}(\text{off}) = -2$ V. Find the values of R_S and R_D , given that $V_{DD} = 20$ V.



5. Determine I_D and V_{GS} for the JFET with voltage-divider bias in circuit shown, given that $V_D = 7$ V.



6. The JFET in the amplifier has a transconductance $g_m = 1 \text{ mA/V}$. If the source resistance R_S is very small as compared to R_G , find the voltage gain of the amplifier.



7. For the JFET amplifier circuit shown, calculate the voltage gain with (i) R_S bypassed by a capacitor (ii) R_S un-bypassed.

